

NX6240GP

Data Sheet

LASER DIODE

1 270 nm AlGaInAs MQW-DFB LASER DIODE

FOR 10 Gb/s E-PON ONU APPLICATION

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Rev.1.00

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DESCRIPTION

The NX6240GP is a 1 270 nm Multiple Quantum Well (MQW) structured Distributed Feed-Back (DFB) laser diode with InGaAs monitor PIN-PD.

APPLICATIONS

- 10 Gb/s E-PON ONU

FEATURES

- | | |
|------------------------------------|--|
| • Optical output power | $P_O = 8.5 \text{ mW}$ |
| • Low threshold current | $I_{th} = 8 \text{ mA}$ |
| • Differential efficiency | $\eta_d = 0.3 \text{ W/A}$ |
| • Wide operating temperature range | $T_C = -5 \text{ to } +85^\circ\text{C}$ |
| • InGaAs monitor PIN-PD | |
| • CAN package | $\phi 5.6 \text{ mm}$ |
| • Focal point | 10.2 mm |



PACKAGE DIMENSIONS (UNIT: mm)

